

S29AL008J

CS Q99814, Q99814a, Q99814b, Q99814c

Qualification of: S29AL008J, 8 Megabit (1 M x 8-Bit/512K x 16-Bit)
CMOS 3.0 Volt-Only Boot Sector Flash Memory in TS048, VBK048,
LAE064 and SSOP56 packages



Reliability Qualification Summary

CONFIDENTIAL

NOTICE: The material in this report is confidential. It is prepared to assist in the qualification of our product. It is declassified for the internal use of our customers only, and may be modified to meet the needs of specific customers. It also serves as a record of full qualification according to JESD47 and AEC-Q100 Grade 1 requirements.

Additionally, the package details (material set, assembly location, etc.) are specific to the qual vehicle used for the qualification. Alternate material sets and assembly locations may be qualified for the product. Production material can be assembled with any qualified material set and at any qualified assembly location. Tests are performed in accordance with AEC-Q100 and relevant JEDEC specifications.

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I.A. Product Information

Product Description: S29AL008J
8 Megabit (1 M x 8-Bit/512K x 16-Bit)
CMOS 3.0 Volt-Only Boot Sector Flash Memory

Package:	TS048	Qualification:	Q99814
Description:	(18.4 x 12.0 x 1.0mm) 48 Lead, Thin Small Outline Package (TSOP)		
Theta Ja:	40 °C/W	Psi Jt:	17 °C/W
Assembly Location:	Spansion Kuala Lumpur	Molding Compound:	RoHS Compliant Epoxy Resin
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Gold
Comments:			

Est. Field Temperature:	55 °C	Life Test Temperature:	150 °C
Est. DC Field Current:	20 mA	Life Test Dynamic Current:	7 mA
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V
Est. Field Power Dissipation:	60 mWatts	Est. Stress Power Dissipation:	25.2 mWatts
Est. Field Tj:	57.4 °C	Est. Stress Tj:	151.0 °C

Die:	98H21B	Die Size:	4.30 x 1.96 mm
Process:	CS69SS (110nm)	Fab:	Spansion Fab25
Type:	Floating Gate	Density:	8M

I.B. Product Information

Product Description: S29AL008J
8 Megabit (1 M x 8-Bit/512K x 16-Bit)
CMOS 3.0 Volt-only Boot Sector Flash Memory

Package:	LAE064	Qualification:	Q99814a
Description:	(9 x 9 x 1.4mm) 64 Ball, Fortified Ball Grid Array Package (fBGA)		
Theta Ja:	39 °C/W	Psi Jt:	11 °C/W
Assembly Location:	Spansion Thailand	Molding Compound:	RoHS Compliant Epoxy Resin
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste
Lead Finish:	96.5Sn3.0Ag0.5Cu Spheres	Bond Wire:	Gold
Comments:			

Est. Field Temperature:	55 °C	Life Test Temperature:	150 °C
Est. DC Field Current:	20 mA	Life Test Dynamic Current:	7 mA
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V
Est. Field Power Dissipation:	60 mWatts	Est. Stress Power Dissipation:	25.2 mWatts
Est. Field Tj:	57.3 °C	Est. Stress Tj:	150.9 °C

Die:	98H21B	Die Size:	4.30 x 1.96 mm
Process:	CS69SS (110nm)	Fab:	Spansion Fab25
Type:	Floating Gate	Density:	8M



I.C. Product Information

Product Description: S29AL008J
8 Megabit (1 M x 8-Bit/512K x 16-Bit)
CMOS 3.0 Volt-only Boot Sector Flash Memory

Package:	VBK048	Qualification:	Q99814b
Description:	(8.15 x 6.15 x 1.0mm) 48 Ball, Very Thin Fine Pitch Ball Grid Array Package (FBGA)		
Theta Ja:	39 °C/W	Psi Jt:	11 °C/W
Assembly Location:	Spansion Thailand	Molding Compound:	RoHS Compliant Epoxy Resin
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste
Lead Finish:	96.5Sn3.0Ag0.5Cu Spheres	Bond Wire:	Gold
Comments:			

Est. Field Temperature:	55 °C	Life Test Temperature:	150 °C
Est. DC Field Current:	20 mA	Life Test Dynamic Current:	7 mA
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V
Est. Field Power Dissipation:	60 mWatts	Est. Stress Power Dissipation:	25.2 mWatts
Est. Field Tj:	57.3 °C	Est. Stress Tj:	150.9 °C

Die:	98H21B	Die Size:	4.30 x 1.96 mm
Process:	CS69SS (110nm)	Fab:	Spansion Fab25
Type:	Floating Gate	Density:	8M



I.D. Product Information

Product Description: S29AL008J
8 Megabit (1 M x 8-Bit/512K x 16-Bit)
CMOS 3.0 Volt-only Boot Sector Flash Memory.

Package:	SSO056	Qualification:	Q99814c
Description:	(23.7 x 13.3 x 2.0mm) 56 Lead, Shrink Small Outline Package (SSOP)		
Theta Ja:	72 °C/W	Psi Jt:	16 °C/W
Assembly Location:	Spansion Kuala Lumpur	Molding Compound:	RoHS Compliant Epoxy Resin
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Gold
Comments:			

Est. Field Temperature:	55 °C	Life Test Temperature:	150 °C
Est. DC Field Current:	20 mA	Life Test Dynamic Current:	7 mA
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V
Est. Field Power Dissipation:	60 mWatts	Est. Stress Power Dissipation:	25.2 mWatts
Est. Field Tj:	59.3 °C	Est. Stress Tj:	151.8 °C

Die:	98H21B	Die Size:	4.30 x 1.96 mm
Process:	CS69SS (110nm)	Fab:	Spansion Fab25
Type:	Floating Gate	Density:	8M

II. CS69SS/LSS Life Test Failure Rate Calculation

HTOL Stress Temperature - 150 °C

Failure Mechanism	Read Points / Test Results				Modeling Parameters @ 55°C					Avg. Failure Rate FITS @ 55°C, 60% Conf.	
	24 hrs	168 hrs	1000 hrs	2000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC											
Sample Size	11200	11334	2370	160							
Zero fails, Process ave. Ea	0 *	0	0	0	0.66	166	1	166		20	1
Totals	0	0	0	0					114155	20	1

* Contributes to early life FITS

Data Retention Bake - 150 °C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate %	Failure Mechanism
500 hrs	0	3400	0.00	No Failures
1000 hrs	0	3900	0.00	No Failures
2000 hrs	0	2000	0.00	No Failures

III. Summary of Stress Test Results

Stress Test	Stress Condition	Package Type	Sample Size	Num. of Lots	Num. of Fails	Failure Rate %	Comments
Data From Qualification Q99814:							
HTOL (EL)	(3.6V, 150°C)	TS048 ¹	77	1	0	0.00	168 hours
ESD CDM	N/A	TS048 ¹	15	1	Passed	1.0kV	
ESD HBM	(100pF, 1500 Ohms)	TS048 ¹	60	1	Passed	2.0kV	
Latch Up	(125°C, +/- 100mA)	TS048 ¹	6	1	Passed		
Endurance (10k)	(125°C, 3.6V)	TS048 ¹	64	1	0	0.00	10k cycles
Endurance (100k)	(125°C, 3.6V)	TS048 ¹	64	1	0	0.00	100k cycles

Generic Reference Data:

HTOL (EL)	(3.6V, 150°C)	TS048 ²	2400	3	0	0.00	24 hours
	(3.6V, 150°C)	TS048 ²	1208	7	0	0.00	168 hours
HTOL (IL)	(3.6V, 150°C)	TS048 ²	900	3	0	0.00	408 hours
Data Retention Bake	(150°C)	TS048 ²	300	3	0	0.00	48 hours
	(25°C)	TS048 ²	3926	3	0	0.00	24 hours
ESD CDM	N/A	VBK048 ³	15	1		Passed 1.0kV	
	N/A	SSO056 ⁴	15	1		Passed 1.0kV	
	N/A	LAE064 ⁵	15	1		Passed 1.0kV	
Preconditioning	(PC1/260°C, +0°C/-5°C)	TS048 ²	693	3		Passed Jedec L3 / Jeita Rank E	
	(PC2/260°C, +0°C/-5°C)	VBK048 ³	231	1		Passed Jedec L3 / Jeita Rank E	
	(PC2/260°C, +0°C/-5°C)	SSO056 ⁴	230	1		Passed Jedec L3 / Jeita Rank E	
	(PC1/260°C, +0°C/-5°C)	LAE064 ⁵	231	1		Passed Jedec L3 / Jeita Rank E	
Precon+Temp Cycle	(PC1/260°C, -40°C/150°C)	TS048 ²	231	3	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	VBK048 ³	77	1	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	SSO056 ⁴	77	1	0	0.00	1000 cycles
	(PC1/260°C, -40°C/150°C)	LAE064 ⁵	77	1	0	0.00	1000 cycles
Precon+HAST	(PC1/260°C, Biased, 130°C/85% RH)	TS048 ²	231	3	0	0.00	96 hours
	(PC1/260°C, Biased, 110°C/85% RH)	VBK048 ³	77	1	0	0.00	264 hours
	(PC1/260°C, Biased, 130°C/85% RH)	SSO056 ⁴	76	1	0	0.00	96 hours
	(PC1/260°C, 3.6V Bias, 110°C/85% RH)	LAE064 ⁵	77	1	0	0.00	264 hours
Precon+Steam Pressure	(PC1/260°C, 121°C/100%RH/15PSIG)	VBK048 ³	77	1	0	0.00	168 hours
Precon+uHAST	(PC1/260°C, Unbiased, 130°C/85% RH)	TS048 ²	231	3	0	0.00	96 hours
	(PC1/260°C, Unbiased, 130°C/85% RH)	SSO056 ⁴	77	1	0	0.00	96 hours
	(PC1/260°C, Unbiased, 130°C/85% RH)	LAE064 ⁵	77	1	0	0.00	96 hours

- Notes / Justification:
- 1) Results from Qual Q99814, S29AL008J, 8M CS69SS (110nm) Floating Gate in 48 Lead TSOP (18.4 x 12 x 1mm)
 - 2) Results from Qual Q99801, S29AL016J in 48 Lead TSOP (18.4 x 12 x 1mm) - Same package, Same Fab and Flash Technology
 - 3) Results from Qual 81282, S29AS016J in 48 Ball vFBGA (8.15 x 6.15 x 1mm) - Same Package, Similar Technology
 - 4) Results from Qual Q99467, S29AL016J in 56 Lead SSOP (23.7 x 13.3 x 2mm) - Same Package and Flash Technology
 - 5) Results from Qual Q06646, S29GL01GR in 64 Ball fFBGA (9 x 9 x 1.4mm) - Same package with larger Die Size

Preconditioning Flows: PC1 (Exceeds JEDEC L3 and JEITA Rank E): Bake 125°C, 24hr => Soak @ 30°C/70%RH, 216hr => 3x Reflow
 PC2 (JEDEC L3): Bake 125°C, 24hr => Soak @ 30°C/60%RH, 192hr => 3x Reflow

IV. Revision History

Section	Description
Revision A - 6/1/2011	
	Initial Release.
Revision B - 6/1/2011	
Section III:Summary of Stress Test Results	Added 168hrs HTOL Reference data

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